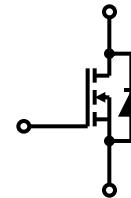


Features

- Low gate charge
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant
- Halogen free package
- JEDEC Qualification

$V_{DSS} = 990 \text{ V} @ T_{j\max}$
 $I_D = 2.5 \text{ A}$
 $R_{DS(ON)} = 5.1 \Omega(\text{max}) @ V_{GS} = 10 \text{ V}$



Absolute Maximum Ratings

Parameter	Symbol	TMP3N90(G)		Unit
Drain-Source Voltage	V_{DSS}	900		V
Gate-Source Voltage	V_{GS}	± 30		V
Continuous Drain Current	$T_C = 25 \text{ }^\circ\text{C}$	I_D	2.5	2.5 *
	$T_C = 100 \text{ }^\circ\text{C}$		1.6	1.6 *
Pulsed Drain Current (Note 1)	I_{DM}	10	10^*	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	16.6		mJ
Repetitive Avalanche Current (Note 1)	I_{AR}	2.5		A
Repetitive Avalanche Energy (Note 1)	E_{AR}	9.4		mJ
Power Dissipation	$T_C = 25 \text{ }^\circ\text{C}$	P_D	94	32
	Derate above $25 \text{ }^\circ\text{C}$		0.75	0.25
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5		V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150		°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	300		°C

Thermal Characteristics

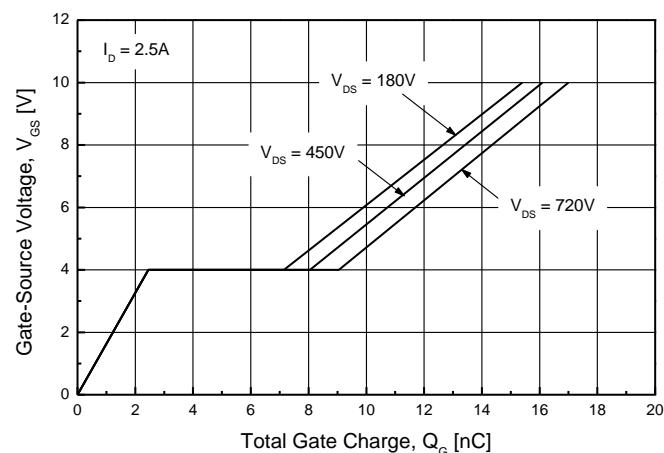
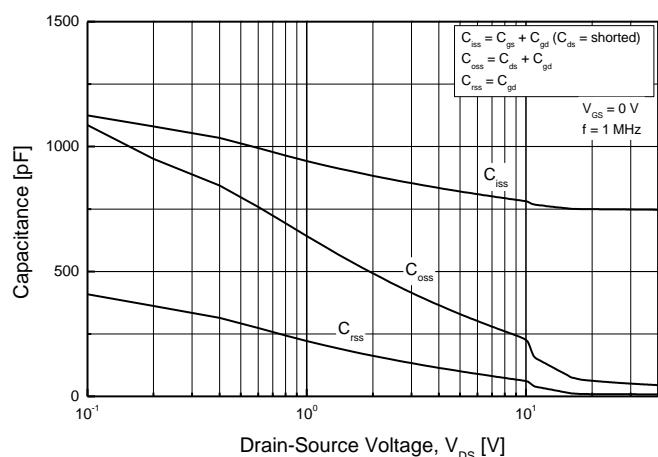
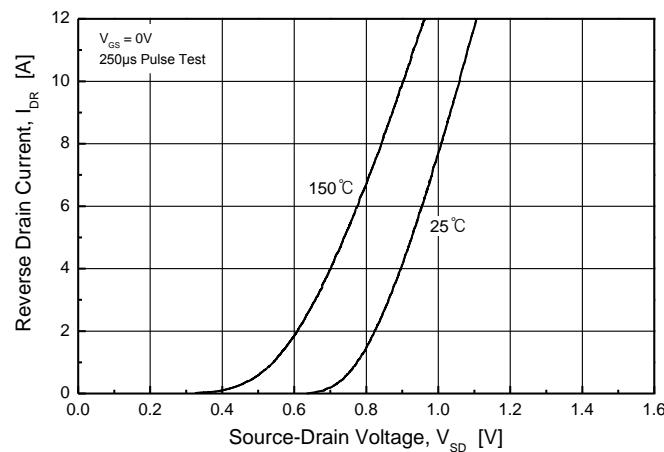
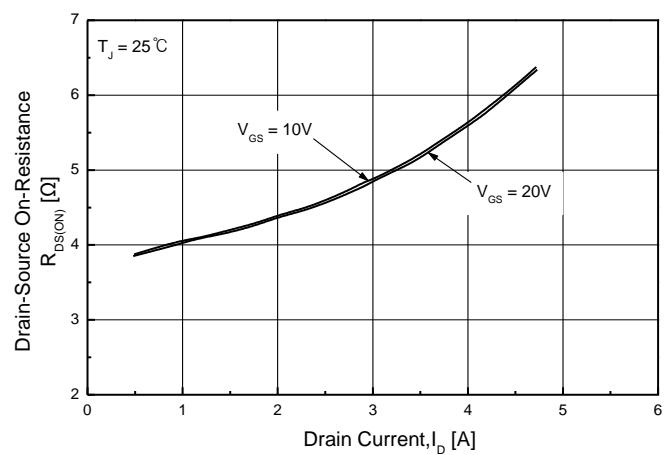
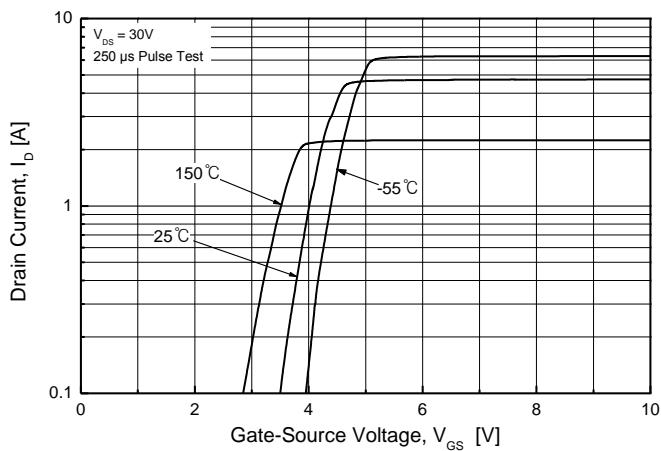
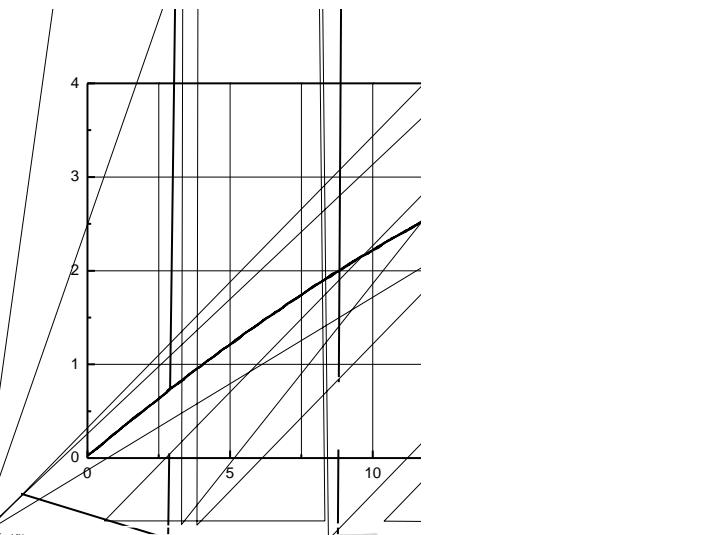
Parameter	Symbol	TMP3N90(G)		Unit
Maximum Thermal resistance, Junction-to-Case	$R_{\theta JC}$	1.33	3.9	°C/W
Maximum Thermal resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	62.5	°C/W

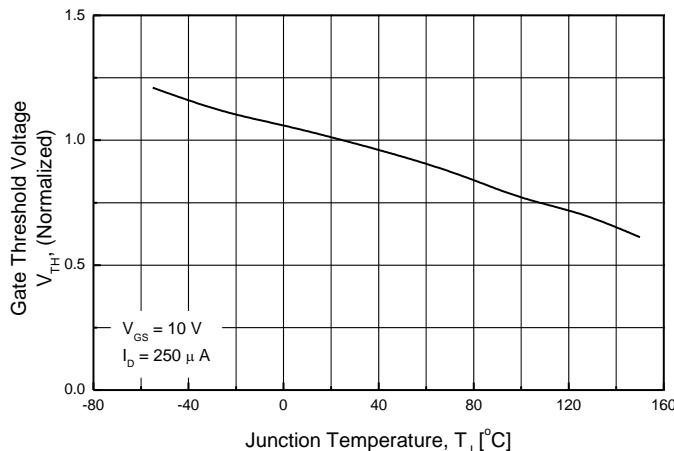
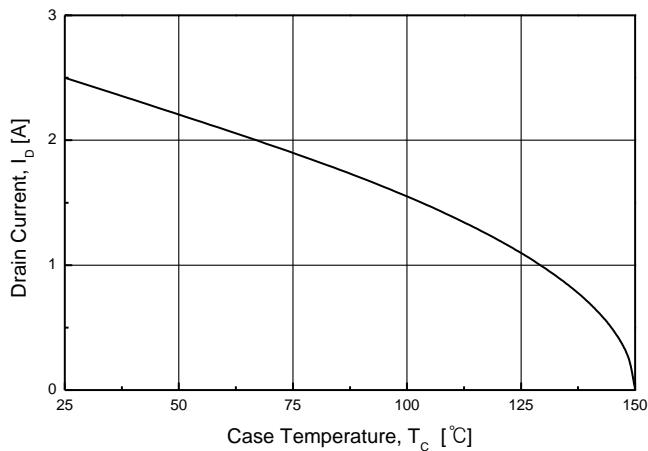
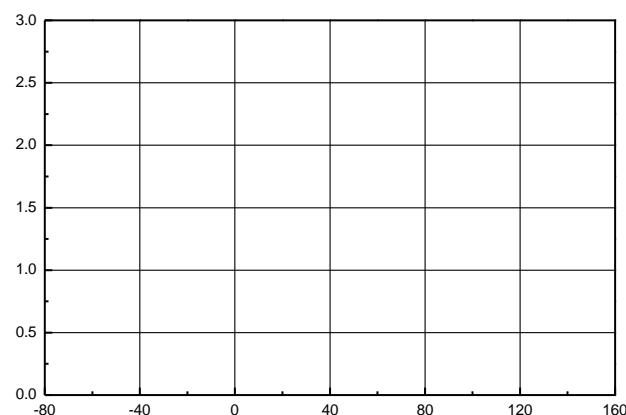
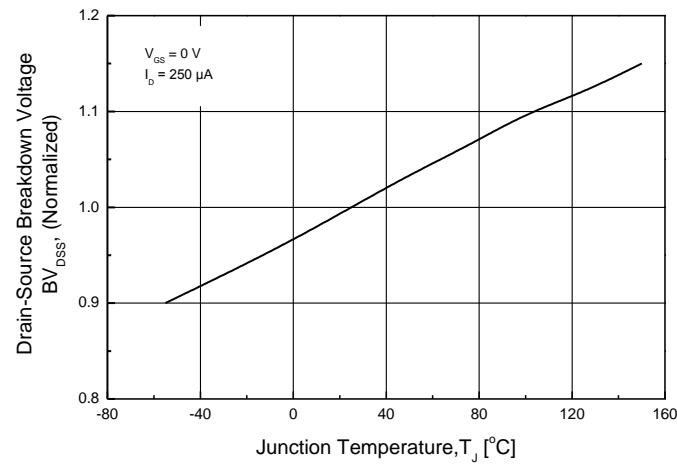
Electrical Characteristics : $T_c=25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test condition	Min	Typ	Max	Units
OFF						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0 \text{ V}, I_{\text{D}} = 250 \mu\text{A}$	900	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 900 \text{ V}, V_{\text{GS}} = 0 \text{ V}$	--	--	10	μA
		$V_{\text{DS}} = 720 \text{ V}, T_c = 125^\circ\text{C}$	--	--	100	μA
Forward Gate-Source Leakage Current	I_{GSSF}	$V_{\text{GS}} = 30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
Reverse Gate-Source Leakage Current	I_{GSSR}	$V_{\text{GS}} = -30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA
ON						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250 \mu\text{A}$	2	--	4	V
Drain-Source On-Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 1.25 \text{ A}$	--	4.3	5.1	Ω
Forward Transconductance ^(Note 4)	g_{FS}	$V_{\text{DS}} = 30 \text{ V}, I_{\text{D}} = 1.25 \text{ A}$	--	3	--	S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 25 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1.0 \text{ MHz}$	--	748	--	pF
Output Capacitance	C_{oss}		--	55	--	pF
Reverse Transfer Capacitance	C_{rss}		--	8.7	--	pF
SWITCHING						
Turn-On Delay Time ^(Note 4,5)	$t_{\text{d(on)}}$	$V_{\text{DD}} = 450 \text{ V}, I_{\text{D}} = 2.5 \text{ A}, R_{\text{G}} = 25 \Omega$	--	16	--	ns
Turn-On Rise Time ^(Note 4,5)	t_{r}		--	25	--	ns
Turn-Off Delay Time ^(Note 4,5)	$t_{\text{d(off)}}$		--	63	--	ns
Turn-Off Fall Time ^(Note 4,5)	t_{f}		--	31	--	ns
Total Gate Charge ^(Note 4,5)	Q_{g}	$V_{\text{DS}} = 720 \text{ V}, I_{\text{D}} = 2.5 \text{ A}, V_{\text{GS}} = 10 \text{ V}$	--	17	--	nC
Gate-Source Charge ^(Note 4,5)	Q_{gs}		--	2.4	--	nC
Gate-Drain Charge ^(Note 4,5)	Q_{gd}		--	6.6	--	nC
SOURCE DRAIN DIODE						
Maximum Continuous Drain-Source Diode Forward Current	I_{s}	---	--	--	2.5	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}	---	--	--	10	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}, I_{\text{s}} = 2.5 \text{ A}$	--	--	1.5	V
Reverse Recovery Time ^(Note 4)	t_{rr}	$V_{\text{GS}} = 0 \text{ V}, I_{\text{s}} = 2.5 \text{ A}$ $dI_{\text{F}} / dt = 100 \text{ A}/\mu\text{s}$	--	355	--	ns
Reverse Recovery Charge ^(Note 4)	Q_{rr}		--	1.8	--	μC

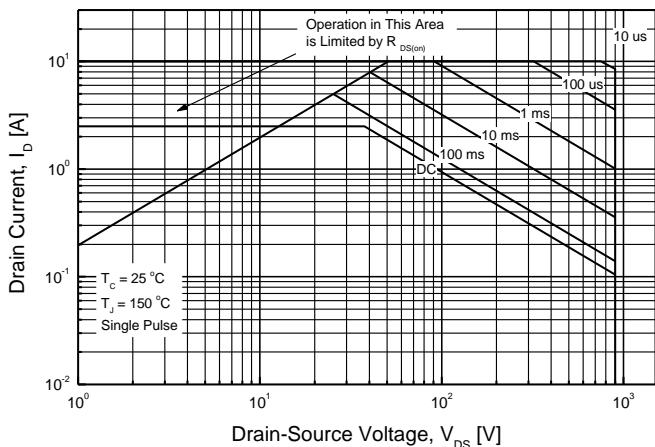
Note :

1. Repeated rating : Pulse width limited by safe operating area
2. $L = 5.0 \text{ mH}, I_{\text{AS}} = 2.5 \text{ A}, V_{\text{DD}} = 50 \text{ V}, R_{\text{G}} = 25 \Omega$, Starting $T_j = 25^\circ\text{C}$
3. $I_{\text{SD}} \leq 2.5 \text{ A}, dI/dt \leq 200 \text{ A}/\mu\text{s}, V_{\text{DD}} \leq \text{BV}_{\text{DS}}$, Starting $T_j = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

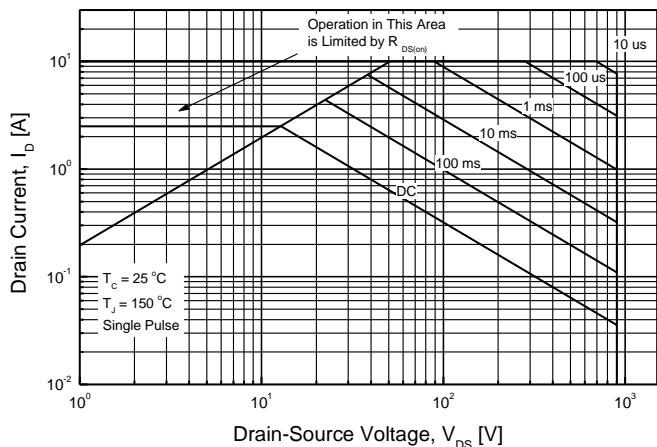


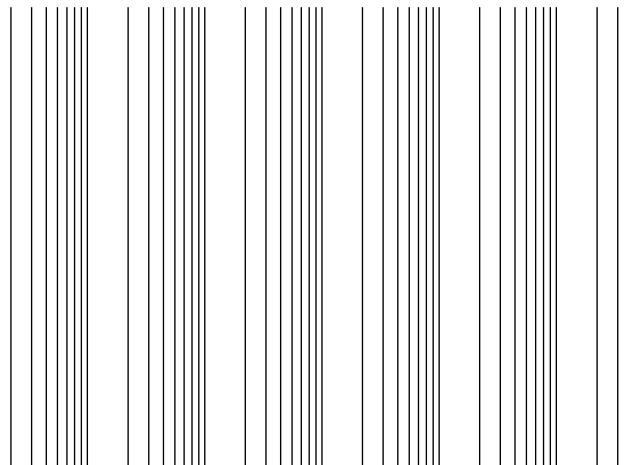
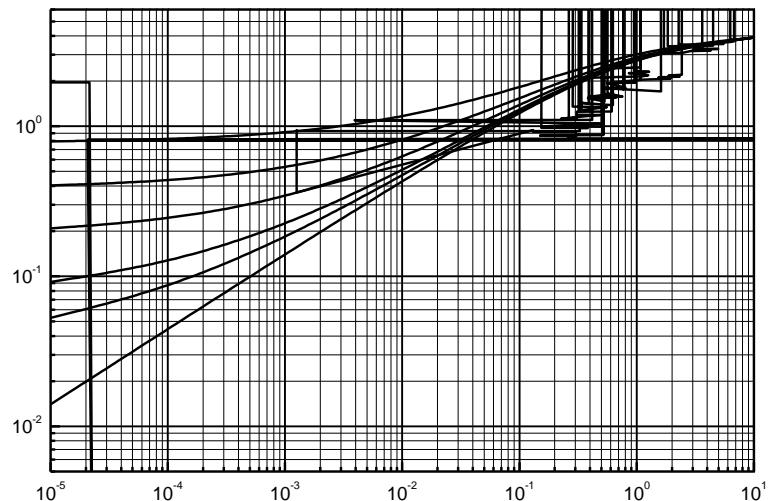


TMP3N90(G)

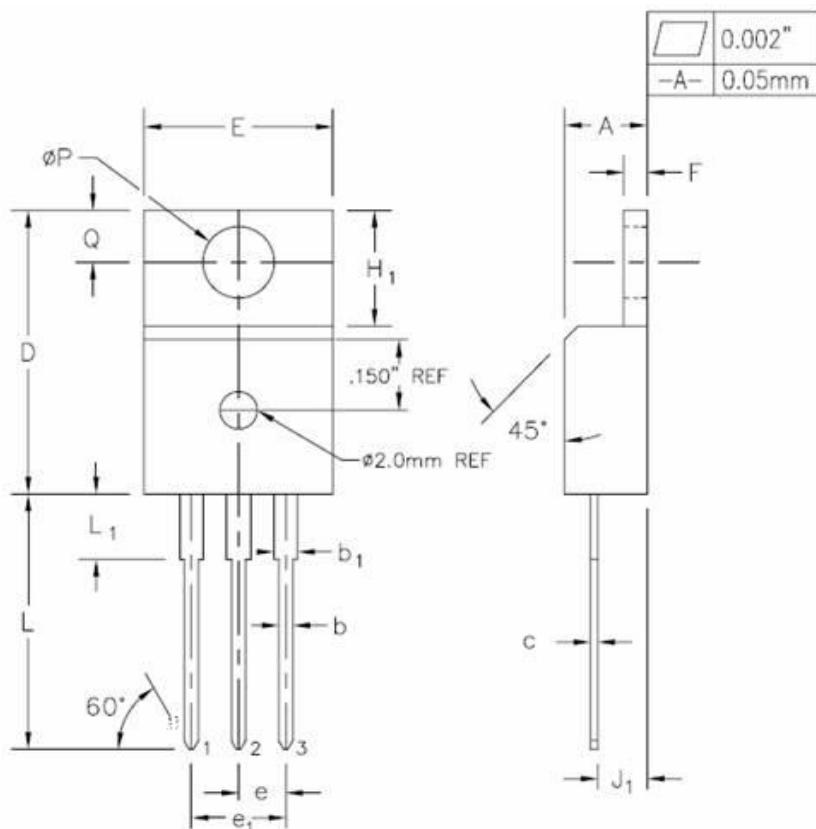


TMPF3N90(G)



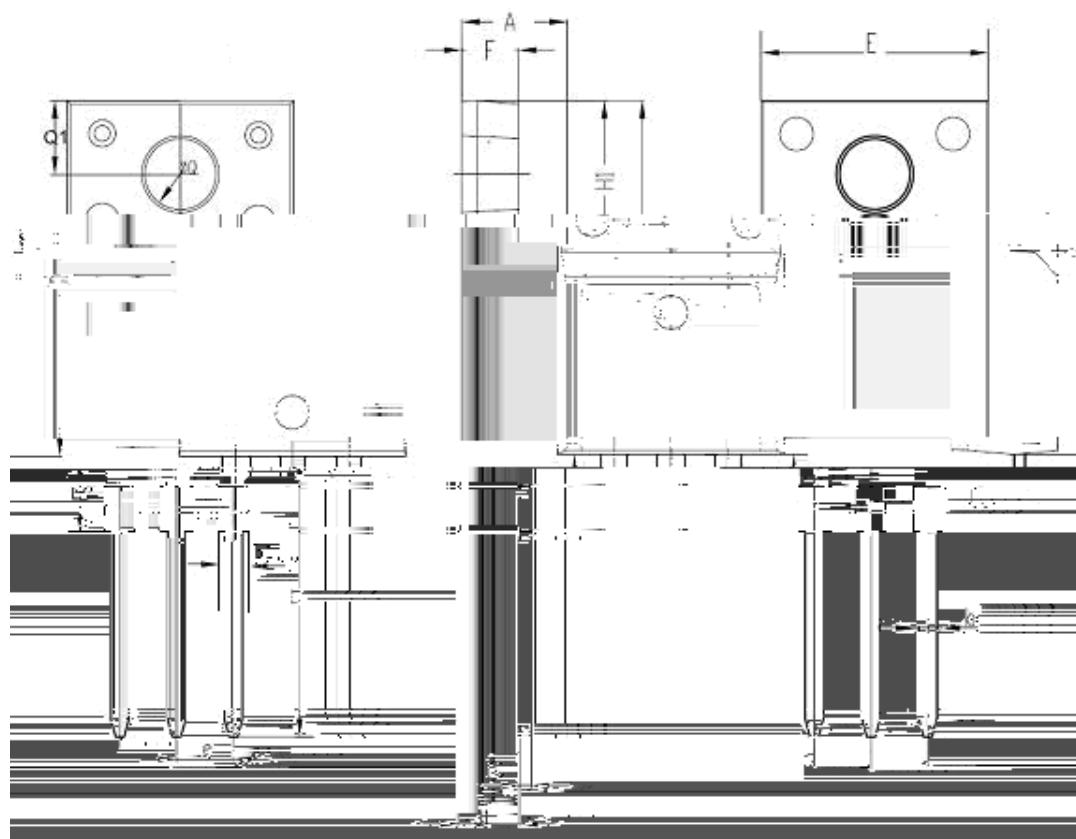
TMP3N90(G)**TMPF3N90(G)**

TO-220AB-3L MECHANICAL DATA



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	0.170	0.180	4.32	4.57	
b	0.028	0.036	0.71	0.91	
b ₁	0.045	0.055	1.15	1.39	
c	0.014	0.021	0.36	0.53	
D	0.590	0.610	14.99	15.49	
E	0.345	0.470	8.76	11.41	
e	0.100	TYP.	2.54	TYP.	
e ₁	0.200	BSC	5.08	BSC	
F	0.048	0.054	1.22	1.37	
H ₁	0.235	0.255	5.97	6.47	
J ₁	0.100	0.110	2.54	2.79	
L	0.530	0.550	13.47	13.97	
L ₁	0.130	0.150	3.31	3.81	2
ϕP	0.140	0.153	3.78	3.86	
Q	0.102	0.112	2.60	2.84	

TO-220F-3L MECHANICAL DATA



NC M	JODI F !		NJMMNF F !!		O F !
	N JO!	N B !	N JO!	N B !	
B!	1 289!!	1 2 5!!	5 64!!	5 4!!	!
!	1 139!!	1 147!!	1 82!!	1 2!!	!
D!	1 129!	1 135!	1 56!	1 71!	!
E!	1 728!!	1 744!!	26 78!!	27 18!!	!
F!	1 4 3!!	1 519!!	7!!	21 47!!	!
!	1 211!	!	3 65	!	!
I 2!	1 367!!	1 383!!	7 61!!	7 1!!	!
2!	1 212!	1 228!!	3 67!!	3 7!!	!
M	1 614!!	1 62 !!	23 89!!	24 29!!	!
φQ!	1 228!!	1 244!!	3 9!!	4 49!!	!
2!	1 156!!	1 166!!	2 26!!	2 4 !!	!
M2!	1 225!	1 241!!	3 !!	4 4!!	!
2!	1 233!!	1 249!!	4 21!!	4 61!!	!
!	1 1 3!	1 219!	3 45!	3 85!	